Im purity-induced transition and im purity-enhanced therm opower in the therm coelectric oxide N aC o₂ $_{x}$ C u_xO $_{4}$

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Various physical quantities are measured and analysed for the Cu-substituted therm celectric oxide $N \approx C_{2 \times} Cu_{x}O_{4}$. As was previously known, the substituted Cu enhances the therm celectric power, while it does not increase the resistivity signi cantly. The susceptibility and the electron speci c-heat are substantially decreased with increasing x, which in plies that the substituted Cu decreases the electron electric comparison with the heavy ferm ion compounds and the valence uctuation systems, we have found that the Cu substitution electric prime increases the coupling between the conduction electron and the magnetic uctuation. The Cu substitution induces a phase transition at 22 K that is very similar to a spin-density-wave transition.

I. IN TRODUCTION

Recently layered cobalt oxides have been extensively investigated as a promising candidate for a therm oelectric material. The therm oelectric material is a material that shows large therm opower (S), low resistivity () and low therm alconductivity () [1], and a quantity $S^2 =$ called the gure of merit characterizes the ofZ therm oelectric conversion e ciency. Therm oelectric device can generate electric power from heat through the Seebeck e ect, and can pump heat through the Peltier e ect. Thus far oxides have been regarded as unsuitable for them oelectric application because of their poor mobility, but som e years ago Terasakiet al. found that a single crystal of the layered oxide N aC o₂O₄ exhibits good therm oelectric perform ance [2]. Fu jita et al. show ed that the dimensionless gure of merit ZT of a NaC QO 4 single crystal exceeds unity at T = 1000 K [3], O htaki et 0:8 at 1000 K even in the polyal. [4] m easured Z T crystalline sam ples of N aC o₂O₄. Thus this compound is quite promising for therm oelectric power generation at high tem perature.

Following NaCo₂O₄, other layered cobalt oxides, Ca-Co-O [5, 6, 7, 8], Bi-Sr-Co-O [9, 10, 11], Tl-Sr-Co-O [12] have been found to show good therm oelectric performance. In particular, Funahashi et al. [8] showed ZT > 1 at 1000 K for Ca-Co-O. The most important feature is that the CdI₂ type triangular CoO₂ block is common to the layered cobalt oxides. We have proposed that the high therm oelectric perform ance of the layered cobalt oxides cannot be explained by a conventional band picture based on the one-electron approximation, but is understood in terms of the strong electron-electron correlation e ects, similarly to the case of heavy-fermion compounds. In fact the material dependence of the therm opower quite resembles that of C eM $_2X_2$ [13].

A prime example for the di culties of the one-electron picture is observed in the Cu substitution e ects in $NaCo_2O_4$ [14]. The therm opower of $NaCo_2 \times Cu_xO_4$ is signi cantly enhanced, while the resistivity is nearly independent of x. This is quite surprising in comparison with normal impurity e ects in a metal. The doped im purity acts as a scattering center in usual cases, and does not make a signi cant change in therm opower, because it is a quantity of the zero-th order of scattering time. Indeed this is what was observed in high-tem perature superconductors [15]. Im portantly, correlation e ects can explain the large impurity e ect on the therm opower, sim ilarly to the case of dilute magnetic alloys [16]. In this paper, we report on measurement of speci c heat, susceptibility, Hallcoe cient, and transverse m agnetoresistance for N aC $o_2 \times C u_x O_4$ polycrystalline sam ples, and discuss the Cu substitution e ects quantitatively.

II. EXPERIMENTAL

Polycrystalline sam ples of $Na_{1:2}Co_{2 \times}Cu_{x}O_{4}$ (x= 0, 0.1, 0.2 and 0.3) were prepared through a solid-state reaction. A stoichiom etric amount of $Na_{2}CO_{3}$, $Co_{3}O_{4}$ and CuO was mixed and calcined at 860 C for 12 h in air. The product was nely ground, pressed into a pellet, and sintered at 920 C for 12 h in air. Since N a tends to evaporate during calcination, we added 20 % excess N a. N am ely we expected sam ples of the nom inal com position

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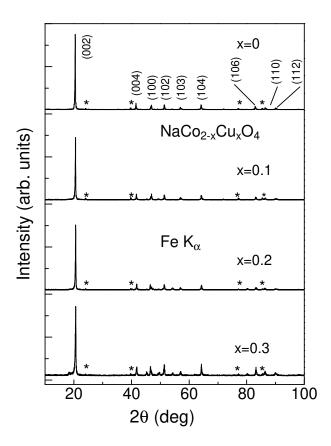


FIG.1: The x-ray di raction patterns of the polycrystalline samples of NaCo₂ $_{x}$ Cu_xO₄. The Fe K is used a an x-ray source.

of $Na_{1,2}Co_{2,x}Cu_{x}O_{4}$ to be $NaCo_{2,x}Cu_{x}O_{4}$.

The x-ray di raction (XRD) was measured using a standard di ractom eter with Fe K radiation as an xray source in the 2 scan mode. The resistivity was m easured through a four-term inalm ethod, and the therm opower was measured using a steady-state technique with a typical tem perature gradient of 0.5 K /cm. The Hall coe cient ($R_{\rm H}$) and the transverse magnetoresistance were measured from 15 to 100 K in a closed refrigerator inserted into a room temperature bore of a liquid-H e free superconducting m agnet. To elim inate the unwanted voltage arising from the misalignment of the voltage pads, the magnetic eld was swept from -7 to 7 T with a typical period of 20 m in at constant tem peratures with a stability of 10 mK. The speci c heat was m easured using a standard relaxation m ethod w ith a m echanical heat switch. The mass of the samples used for the measurement is typically 1000 mg and the heat capacity of the sam ples is always more than two orders of m agnitude larger than the addenda heat capacity. The susceptibility was measured with a SQUID susceptom eter in a magnetic eld of 1 T.

III. RESULTS

Figure 1 (a) shows the x-ray di raction patterns of the prepared sam ples of $NaCo_{2 \ x} Cu_xO_4$. A lm ost all the peaks are indexed as the phase [17, 18], though a sm allam ount (approxim ately less than 5%) of unreacted Co_3O_4 is observed. W ith increasing Cu content x, no additional peak appears, with the patterns unchanged, which shows that Cu is substituted for Co. How ever, the sam ple of x = 0.3 shows a higher background noise, indicating that the crystal quality becomes worse, possibly ow ing to the lim it of solution with Cu.

Figure 2(a) shows the tem perature dependence of the resistivity for $N \ aCo_{2 \ x} Cu_x O_4$. All the samples are metallic down to $4.2 \ K$ without any indication of localization. It should be noted that the increased resistance due to the substituted Cu is of the order of 10 cm for 1 at.⁸ Cu, which is anom alously small in the layered transition-metal oxides [19]. Another important feature is that the resistivity for the Cu substituted samples show a kink near 22 K as indicated by the dotted line. Since the tem perature dependence is steeper below 22 K, the density of states (or the carrier concentration) decreases below 22 K.

Figure 2 (b) shows the temperature dependence of the therm opower for $NaCo_{2 \ x} Cu_x O_4$. Therm opower increases with increasing x with a dip near 22 K and a peak

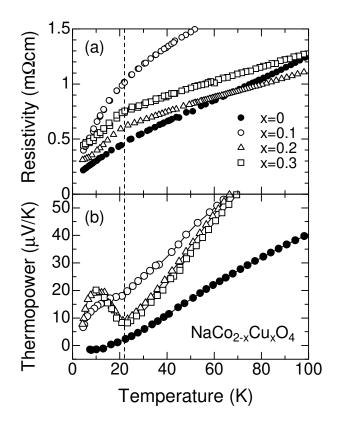


FIG.2: (a) The resistivity and (b) the therm opower of polycrystalline samples of NaCo2 $_x$ C u_x O $_4$.

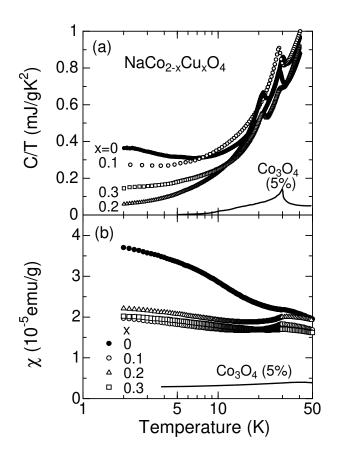


FIG. 3: (a) The speci c heat C and (b) the susceptibility of polycrystalline samples of N aC $o_2 \times C u_x O_4$. Note that C=T is plotted in order to emphasize the electron speci c heat coe cient . The samples include 5% of unreacted C $o_3 O_4$, and the data for 5% C $o_3 O_4$ taken from R efs, [20, 21] are plotted by the solid curves.

near 10-15 K. A swe previously shown in the analysis for BiSr-Co-O [10], a low-tem perature them opower (S) of the layered Co oxides is determ ined by the di usive tem that is proportional to tem perature (T). A coordingly S=T is an essential parameter similarly to the electron speci c-heat coe cient. Thus, the dip, rather than the peak, is a meaningfultem perature, which corresponds to the onset of the enhancement in S=T at low tem perature is nearly the same as the kink tem perature for the resistivity, which strongly suggests that this tem perature is related to a kind of phase transition.

Figure 3(a) shows the specic heat C for $NaCo_{2 x}Cu_{x}O_{4}$. In order to emphasize the T-linear electron specic cheat, we plot C=T as a function of temperature. As shown in Fig. 3(a), the C=T value at 2 K decreases with increasing the Cu content from 0 to 0.2, which means the decrease of the electron specic cheat coe cient with x. (For the sample of x= 0.3, the C=T value increases again, which might be due to an extrinsic origin such as the solid-solution limit of Cu.) Since is proportional to the density of states and the

mass-enhancem ent factor, the present results indicate that the either or both decrease with the Cu substitution. As for high tem peratures, all the data show a peak near 30 K which is the antiferrom agnetic transition of the unreacted Co_3O_4 , as shown by the solid curve [20]. A sm entioned above, the x-ray di raction patterns reveal less than 5 at % of unreacted Co₃O₄, which is consistent with the peak height of the speci c heat at 30 K.We should emphasize here that the existence of Co_3O_4 does not seriously a ect the estimation of , because the C = T value for Co_3O_4 is negligibly small at low temperatures. For x = 0.2 and 0.3, another peak appears in the speci c heat near 22 K, which is close to the kink temperature in , and the dip temperature in S.W e thus conclude that the 22-K anom aly com es from a (2nd order) phase transition.

() of Figure 3(b) shows the susceptibility $NaCo_{2 \times} Cu_{\times}O_{4}$. The substituted Cu also decreases the susceptibility, indicating the decrease of the density of states and/or the mass-enhancement factor. Α broad hump near 30 K is due to the antiferrom agnetic transition of the unreacted $C o_3 O_4$, as shown by the solid curve [21]. Interestingly, there is no anom aly near 22 K in the susceptibility, suggesting that the transition at 22 K is not the magnetic transition of impurity phases. We further note that the Curie-like contribution is absent in the susceptibility at low temperatures, which shows that m agnetic in purities are unlikely to exist other than Co_3O_4 . Quantitatively, the decrease of by Cu is more m oderate than that of $C = T \cdot C = T$ decreases by a factor often from x = 0 to 0.2, whereas decreases only by a factor of two. This implies that the 22-K transition causes a dramatic reduction of the electron entropy possibly owing to a (pseudo)gap formation, while it does not alter the magnetic excitation at k = 0. The nature of the 22-K transition will be discussed in the next section.

Figure 4(a) shows the Hall coe cient ($R_{\rm H}$) of NaCo_{2 x} Cu_xO₄. The sign is negative below 100 K, and the magnitude is as small as 4-6 10 ⁴ cm ³/C. The Cu substitution does not change the magnitude so much, indicating that the carrier concentration is nearly unchanged. By contrast, it changes the temperature dependence in a complicated way, which implies that plural kinds of carriers are responsible for the electric conduction. The band calculation by Singh [22] reveals that the two bands of di erent symmetries cross the Ferm i level for NaCo₂O₄. (See the next section)

Contrary to the Hall e ect, the magnetoresistance is weakly dependent on the Cu substitution, as shown in Fig. 4(b). By taking a closer look at the x dependence, one can see that the negative magnetoresistance is gradually suppressed by the substituted Cu. This im plies that the kink of the resistivity is more or less sm eared against magnetic eld, which suggests that the magnetic eld suppresses the 22-K transition.

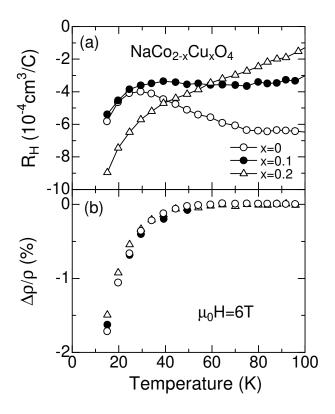


FIG.4: (a) The Hall ∞ e cient R_H and (b) the magnetoresistance = of polycrystalline samples of N aC Q x C u_xO 4.

IV. D ISC U SSIO N

Before going into details, we will begin with a brief review on the electronic states of NaCo₂O₄. As is well known, the ve-fold degenerate d orbitals split into twofold (eq) and three-fold (t_{2q}) degenerate levels in an oxygen octahedron. In the real triangular $C \circ O_2$ block, the octahedron is compressed along the c direction, and the degeneracy is further quenched, where the lower t_{2q} levels split into eq and alq levels. The low er eq levels correspond to the orbital spread along the CoO_2 block to make a relatively broad band, whilst the $a_{1\alpha}$ orbital is spread along the c direction to make a nearly localized narrow band. Since each Co ion is 3.5+ with $(3d)^{5:5}$, the highest occupied orbital is a_{1q} in the atom ic lim it, and the main part of the Ferm i surface consists of the narrow alg band. In the real band calculation, how ever, there is signi cant hybridization between the a_q and e_q levels, and the broader $e_g + a_{1g}$ band touches the Ferm i level to make smallFerm i surfaces [22].

We have proposed that the electronic structure of $N \ aC \ o_2 O_4$ is similar to that of the C e-based interm etallics, a prime example of valence- uctuation/heavy-ferm ion compounds [13]. and of $N \ aC \ o_2 O_4$ are as large as those of C eP d₃. In this context, the large therm opower of $N \ aC \ o_2 O_4$ is explained in term s of a di usive contribution of a metal with a heavily enhanced e ective mass, and is roughly proportional to . In the heavy ferm ion

com pounds, the broad conduction band crosses the Ferm i energy, and the narrow (localized) fband is located below the Fermi energy. For N aC o_2O_4 , the broad $e_q + a_{1q}$ band and the narrow a_{1q} band do exist, but both of which cross the Fermi energy to form two kinds of the Fermi surfaces. Thus it is not trivial whether or not the two Ferm i surfaces behave heavy-ferm ion-like in the charge transport. At least we can say that the two Fermi surfaces play di erent roles, where the Cu substitution induces di eris weakly dependent on the Cu content x, ent e ects: whereas S, and are strongly dependent on x. S, and are basically proportional to the density of states in the lowest order, which are determined by the large Ferm i surface of the alg sym metry. In contrast, the carriers on the $e_g + a_{1g}$ band can be highly mobile, because it is spread along the in-plane direction. In short, the a_{1g} and $e_{g} + a_{1g}$ bands are responsible for the large therm opower and a good electric conduction, respectively.

Existence of the a_{1g} and $e_g + a_{1g}$ bands was suggested from the angular dependence of the X-ray absorption spectroscopy experiment [23, 24], where the valence bands of N aC o_2O_4 consist of the a_{1g} and $e_g + a_{1g}$ bands. The valence band of the less conductive B iSrC o-O is mainly composed only of the a_{1g} band, which is consistent with our speculation that the $e_g + a_{1g}$ band is responsible for the m etallic nature of N aC o_2O_4 . The large Ferm i surface suggested by the band calculation was not seen in the angle photoem ission spectra for B iSrC o-O, which indicates that the band calculation should be modie i ed by additional eects such as the electron-electron or electron-phonon e ects.

A. Phase Transition at 22 K

As shown in the previous section, the Cu substitution causes the phase transition at 22 K, which is probed by the jump of the speci cheat, the dip in the therm opower, and the kink in the resistivity. Figure 5 (a) shows the speci cheat for the x = 0.2 sample (the same data in Fig. 3 (a)) as a function of temperature in linear scale in order to see the 22-K anom aly clearly. One thing to point out is that the entropy change of this transition is surprisingly sm all. As shown in Fig. 5 (a), we estimated the entropy change by the area surrounded with C =T and the dotted line, which is approximately 77 m J/K m ol, corresponding to 0.01k_B per Co. A ctually only 5% of Co₃O₄ in purity exhibits a speci cheat jump of the same order at 30 K.

There are two possibilities for the origin of the small entropy change. One is that the 22-K transition is something related to the inpurity phase of the order of 1%. A lthough we cannot exclude this possibility completely, we will take the other possibility that the small entropy change is an intrinsic nature in bulk, because (i) the eld dependence of C=T is di erent between the 22-K transition and the magnetic transition in Co_3O_4 at 30 K as shown in Fig. 5 (b), (ii) a possible in purity phase is a Cu-based magnetic material, which is inconsistent with

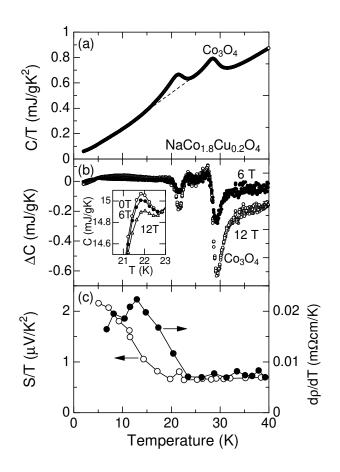


FIG. 5: Phase transition at 22 K for the Cu-substituted sample (x=0.2). (a) Speci c heat, (b) m agneto-speci c heat C (H) C (H) C (0), and (c) temperature derivative of the resistivity d =dT and the T-linear coe cient of the thermopowerS=T.The inset shows the magnetic eld dependence of the speci cheat.

no anom aly in at 22 K, and (iii) the therm opower and the resistivity system atically change at the sam e tem perature. The most fam iliar phase transition accompanied by a small entropy change is perhaps superconducting transition. M ore generally, o -diagonal long range order induces a sm allentropy change of the order of N k_B T = E $_F$.

Figure 5(c) shows the T-linear term of the therm opower (S=T) and the tem perature derivative of the resistivity d =dT, both of which are inversely proportional to the D rude weight [25]. T heir tem perature dependences are quite sim ilar to each other, where the magnitude increases up to almost twice below 22 K. This indicates that the D rude weight decreases by 50% at low tem peratures, implying the existence of a (pseudo)gap. As an o diagonal long-range order with a gapped state, one would think of charge density wave (CDW) or spin density wave (SDW). The calculated Ferm isurface [22] of the alg band is hexagon-like, which is unstable against CDW or SDW form ation with the nesting vector along the -K direction. W e think that the 22-K transition is SDW -like, because CDW is insensitive to magnetic eld [26]. A ctually

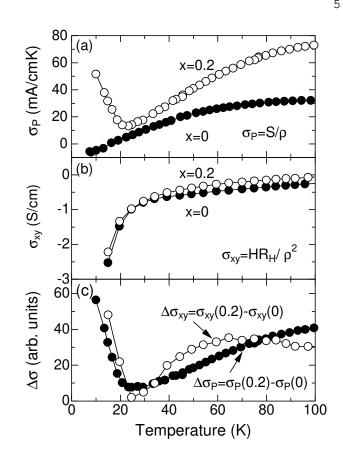


FIG.6: (a) Peltier conductivity P = S = (b) Hall conductivity $xy = HR_{H} = {}^{2}$ for the x = 0 and x = 0.2 samples (c) the relative change in P and xy from x = 0 to 0.2

we can nd m any sim ilarities between the 22-K transition and SDW transition: The entropy change is observed to be quite sm all in Cr [27], YbB iPt [28] and (TM TSF)₂PF₆ [29]. The resistivity shows a hump [27, 28], and the therm opower shows a dip at the transition [30].

It is not surprising that the 22-K transition has little effects on the magnetic susceptibility. Since an SDW state is an antiferrom agnetically ordered state, the magnetic excitation is gapless in principle. In fact, the SDW state of Crexhibits a very tiny (1-2%) change in the susceptibility at the transition tem perature [27], while it causes a clear hump in the resistivity [31]. The metallic conduction below 22 K, im plies that a part (approxim ately 50%) of the Ferm i surface remains, which could sm ears the SDW transition. To clarify the nature of the transition, a localm agnetic probe such as NMR or SR should be em ployed.

в. Ε ects on the Hall coe cient and therm opower

Next we will discuss how we can understand the Cu substitution e ects on $R_{\!H}\,$ and S . W e should note here that the sum rules of transport parameters for a multiband system are expressed in the form of conductivities,

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not in the form of R_H or S. Let us denote the conductivities for the a_{1g} and $e_g + a_{1g}$ bands as ^a and ^e, respectively. The total conductivity is then written as

$$= e^{e} + a$$
 (1)

Similarly, the total H all conductivity x_y and the total Peltier conductivity $_P$ are written as

$$xy = \begin{array}{c} e \\ xy \end{array} + \begin{array}{c} a \\ xy \end{array}$$
(2)

$$P_{P} = P_{P}^{e} + P_{P}^{a}$$
(3)

where the Peltier conductivity [32] is defined as $_{\rm P}$ S = S= .

Figure 6(a) show sthe tem perature dependence of $_{\rm P}$ = S= for x = 0 and 0.2. The Cu substitution enhances the Peltier conductivity over the measured tem perature range from 4 to 100 K, indicating that the mobility is enhanced by Cu. The enhancement below 22 K is more remarkable in $_{\rm P}$ than in S, which indicates the mobility is rapidly enhanced below the 22-K transition. Figure 6(b) shows the tem perature dependence of $_{\rm XY}$ = H R_H = 2 for x = 0 and 0.2. The com plicated change seen in R_H is converted into a simpler change in $_{\rm XY}$. Although the Cu substitution e ects in is quite small, 1= 2 term moderates the di erence in R_H. O ne can see that $_{\rm XY}$ is also increased by Cu over the tem perature range from 15 to 100 K, as is similar to the case of $_{\rm P}$.

Let us assume that the substituted Cu a ects only the a_{1g} band. Then a di errence between x = 0 and 0.2 is reduced to a change in P_{P}^{a} and P_{XY}^{a} . Figure 6(c) shows ху = $_{\rm P} = _{\rm P} (x = 0.2)$ $_{\rm P}$ (x = 0) _{xy} (x = xy (x = 0). Most unexpectedly, the change in 0:2) the Peltier conductivity P and the change in the Hall conductivity xy show nearly the sam e tem perature dependence. In particular, a clear enhancem ent below 22 K indicates that the phase transition causes an equal in pact on S and R_H in the form of the Peltier and Hall conductivities.

On the assumption that only the a_{1q} band is modi ed by Cu, we will consider the change in the a_{1g} band in term softhe carrier concentration n, the e ective m assm, and the scattering time \cdot . Then $_{P}^{a}$ and $_{xy}^{a}$ are roughly hn=m iand ^axy expressed as $\frac{a}{p}$ $h_{R} = m_{i}$, where the average of h i is de ned as 14^1 (v_F)² ³k dA close sim ilarity between $_{\rm P}$ and xy implies that h i and hniare nearly independent oftem perature. The Tindependent h imeans the scattering time averaged in the alg Ferm i surface is dom inated by impurity scattering, which is consistent with the localized picture of the a_{1g} band. The positive values of _{xv} and P suggests that the increase of h1=m i. This indicates that the mass enhancem ent is suppressed (the m obility is enhanced) by Cu over the measured tem perature range, regardless of the 22-K transition, which is consistent with the decrease in and by Cu.

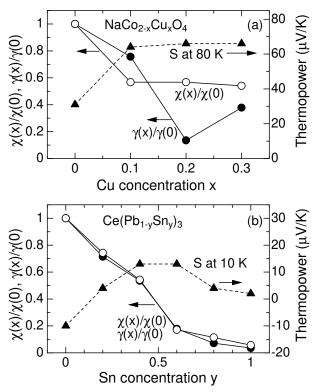


FIG.7: (a) Cudependence of , and S of N aC $_{0_x}$ Cu_xO $_4$. (b) Sn dependence of , and S of Ce(P b_{1_y} Sn_y) $_3$.

C. Comparison with Ce based compounds

Based on the heavy-ferm ion scenario, it seems inconsistent that the substituted Cu causes the decrease in (Fig. 3) together with the increase in S (Fig. 2). As shown in Fig. 7(a), , and S are plotted as a function of the Cu content x. (Note that was estimated as C=T at 2 K, and was estimated as the raw value of at 2 K.) Although and decreases with x, S signi cantly increases with x, where S / is no longer valid.

We should emphasize that the relationship between and S is complicated also in the Ce-based compounds. Figure 7(b) shows , [33] and S [34] for Ce(Pb₁ y Sn_y)₃ as a function of the Sn content y. CePb₃ is in the heavy ferm ion regime (low K ondo temperature) and CeSn₃ is in the valence uctuation regime (high K ondo temperature). Thus the solid solution between Pb and Sn changes the material from the heavy-ferm ion to the valenceuctuation compound, which is evidenced by the fact that and monotonically decrease with y. On the other hand, S exhibits complicated y dependence. S is negative for y = 0, increases with y up to 0.4, and eventually decreases from y=0.6 to 1.0.

This is intuitively understood as follows. When the K ondo temperature is su ciently low as in the case of $CePb_3$, the RKKY interaction survives at low temperatures, and often causes a magnetic transition. Since

the magnetic transition release the entropy of the spin sector, the entropy per carrier (equivalently the di usive term of the therm opower) would be suppressed against the uctuation of the magnetic transition. On the other hand, when the K ondo tem perature is high enough, the mass enhancement is severely suppressed to give a small therm opower again. Thus the therm opower would take a maximum at an intermediate value of the K ondo tem – perature. This is indeed what we see in Fig. 7 (b), and similar to the general trend of the 20-K therm opower of $C \text{ eM}_2 X_2$ found by Jaccard et al.[35]

In this context, the N aC o_2O_4 is located near the heavy-ferm ion regime, and the substituted Cu caused the decrease in the mass enhancement accompanied by the increase in S, which is consistent with the increase in the Peltier and H all conductivities seen in the previous subsection. A lthough there is no m icroscopic relationship between N aC $o_2 \times Cu_xO_4$ and $Ce(Pb_1 \times Sn_y)_3$, a close resemblance in Fig. 7 suggests that the unsubstituted N aC o_2O_4 corresponds to y 0.2, while N aC $o_{1.8}Cu_{0.2}O_4$ corresponds to y 0.4 0.6. We further note that the Pd substituted N aC o_2O_4 show snegative therm opower below 50 K, which m ight correspond to y < 0.2 [36].

D. Order from disorder

A lthough the m icroscopic theory for the high therm oelectric perform ance of N aC o_2O_4 is still lacking, the following features are established. (1) The m ixture of C o^{3+} and C o^{4+} in the low spin state can carry a large entropy of $k_B \log 6$ [37]. (2) N aC o_2O_4 shows no structural, electric, and m agnetic transitions from 2 to 1000 K [3, 4]. (3) From (1)(2), the large entropy cannot be released through phase transitions, and inevitably adhere to the conducting carriers to form a \heavy-ferm ion"-like electron.

In this respect, N aC o_2O_4 is very close to the instability for various phase transitions arising from the large entropy per site. The Cu substitution enhances the instability, and eventually causes the SDW -like transition at 22 K. This type of transition is called \order from disorder" [38], which has been extensively investigated experim entally as well as theoretically. In other words, instabilities against various phases are competing or disordering in NaCo204, and any phase transitions are prohibited down to low temperatures. This does not mean that $N \approx O_2 O_4$ is far from the instability of phase transitions, but rather, is very susceptible to various transitions against various perturbations. In fact, N $a_{1:5}C o_2O_4$ exhibits a glassy behavior at 3 K due to structure instability of the phase [39], and (Bi,Pb)-Sr-Co-O shows a ferrom agnetic transition at 4 K due to the lattice m is t [40].

A m ong various possible transitions, it is not trivial whether an SDW -like state is favored by impurities or not. As an SDW -form ation m echanism, we should note here that SDW and CDW are closely related to the nest-

ing of the and the topology of the Ferm i surface. They are a property for a metal, and occur when the correlation e ect is weak enough to hold one-electron picture based on the band calculation. As offen mentioned in the present paper, the experimental results consistently suggest that C u suppresses the mass enhancement without signicant change in the carrier concentration. If so, the decrease in implies that the substituted C u enhances the screening of the magnetic uctuation, which might recover the band picture to cause the CDW /SDW instability of the alg Ferm i surface.

V. SUMMARY AND FUTURE ISSUES

In this article, we have discussed the Cu substitution e ects on the them oelectric and them odynam ic properties of N aC o_{2 x} Cu_xO₄. The substituted Cu induces a phase transition at 22 K, which is characterized by the kink in the resistivity, the hump in the them opower, and the jump in the speci c heat. We have analysed the nature of the transition, and nally proposed a spindensity-wave-like state as a possible origin, because (i) it accompanies a small entropy change of the order of 10 2 k_B perCo, (ii) the transition is sensitive to them agnetic eld, (iii) the large Ferm i surface of the $a_{\rm g}$ character is gapped. The impurity induced transition is offen called \order from disorder", which in plies that phase transitions are somehow suppressed in the unsubstituted N aC o₂O $_4$.

Above the transition tem perature, the therm oelectric properties are at least qualitatively compared with those of heavy-ferm ions valence- uctuation compounds, where m oble holes on the $e_g + a_{1g}$ band and the nearly localized holes of the a_{1g} band correspond to the carrier and the f electrons. In this analogy, the substituted Cu increase the interaction between the $e_g + a_{1g}$ and a_{1g} bands to decrease the e ctive-m ass enhancement.

In this article we have reviewed the phenomenology of the Cu substitution e ects, but failed to address the m icroscopic origin and/or the electronic states of the substituted Cu. This is because our experiments were concerned only with the therm odynam ic and transport properties of bulk materials. Nonetheless we can say that the scattering cross section will be small for the d_{x^2} $_{y\ ^2}$ and d_{z^2} levels of the impurity in NaCo2O $_4$, because the valence bands of N aC $o_2 O_4$ consist of t_{2q} . Thus the substituted Cu (possibly divalent [41]) will not inseriously, because Cu^{2+} has the highest occucrease pied orbital of $d_{x^2 v^2}$ that is orthogonal to t_{2g} . In addition, strong Jahn-Teller e ects of $C u^{2+}$ m ay cause local distortion of the CoO_2 block, which serves as a kind of chem ical pressure to increase S [13]. To proceed further, site-selective probes such as NMR, photoem ission, and STM /STS should be employed.

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